



Docket No: 740756-2675

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Divisional Patent Application of )  
Hongyong ZHANG )  
Application Serial No. 10/726,529 ) Art Unit: 2823  
Filed: December 04, 2003 ) Examiner: K. Nguyen  
For: METHOD FOR FORMING A )  
SEMICONDUCTOR DEVICE ) Date: January 22, 2004

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure as set forth in 37 C.F.R. §1.56, Applicants hereby submit the following information in conformance with 37 C.F.R. §§ 1.97 and 1.98.

The references listed on the attached Form PTO-1449 were cited in parent application Serial No. 09/222,776 filed December 30, 1998, and its predecessors application Serial Nos. 08/300,938 and 07/956,860, from which priority is claimed under 35 U.S.C. 120. Consequently, copies of the documents are not required.

It is requested that the accompanying PTO-1449 be considered and made of record in the above-identified application. To assist the Examiner, the documents are listed on the attached form PTO-1449. It is respectfully requested that an Examiner initialed copy of this form be returned to the undersigned.

Respectfully submitted,

By

  
Jeffrey L. Costellia  
Registration No. 35,483

NIXON PEABODY LLP  
401 9<sup>th</sup> Street, N.W.  
Suite 900  
Washington, D.C. 20004-2128

(202) 585-8000  
NVA283469.1



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PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

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| <b>Substitute for form 1449A/PTO</b><br><br><b>INFORMATION DISCLOSURE<br/>STATEMENT BY APPLICANT</b><br><br><i>(use as many sheets as necessary)</i> |           |    |   | <b>Complete if Known</b> |                  |
|  |           |    |   | Application Number       | 10/726,529       |
|  |           |    |   | Filing Date              | December 4, 2003 |
|  |           |    |   | First Named Inventor     | Hongyong ZHANG   |
|  |           |    |   | Group Art Unit           | 2823             |
| Examiner Name  | K. Nguyen |    |   |                          |                  |
| Sheet  | 1         | of | 4 | Attorney Docket Number   | 740756-2675      |

| U.S. PATENT DOCUMENTS             |                          |                      |                                      |  |  |   |
|-----------------------------------|--------------------------|----------------------|--------------------------------------|--|--|---|
| Examiner<br>Initials <sup>1</sup> | Cite<br>No. <sup>1</sup> | U.S. Patent Document |                                      | Name of Patentee or Applicant<br>of Cited Document | Date of Publication of<br>Cited Document<br>MM-DD-YYYY | Pages, Columns, Lines,<br>Where Relevant Passages or<br>Relevant Figures Appear |
|                                   |                          | Number               | Kind Code <sup>2</sup><br>(if known) |  |  |   |
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| <b>Examiner<br/>Signature:</b> | <b>Date<br/>Considered:</b> |
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



Sheet 3 of 4Form PTO-1449  
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Patent and Trademark Office

Attorney Docket:

740756-2675

Serial No.

10/726,529

**INFORMATION DISCLOSURE STATEMENT**

(Use several sheets if necessary)

Applicant: Hongyong ZHANG

Filing Date: December 4, 2003 Group: 2823

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

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Examiner

Signature:

Date

Considered:

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**Form PTO-1449**  
(Rev. 8-83)

Department of Commerce  
Patent and Trademark Office

**Attorney Docket:**

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Serial No.

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**Applicant:** Hong ZHANG

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|--------------------------------------|--------------------|

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

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